

CLAIM AMENDMENTS

1.-10. (Cancelled)

11. (Original) A semiconductor structure comprising:
a gate; and
an implanted region including both germanium and P-type impurities.

12. (Original) The structure of claim 11 wherein the ratio of germanium to P-type impurities is greater than one to one.

13. (Original) The structure of claim 12 wherein the ratio of germanium to P-type impurities is approximately four to one.

14. (Original) The structure of claim 13 wherein said P-type impurities are boron impurities.

15. (Original) The structure of claim 11 wherein said germanium is implanted to a depth greater than about 150 Angstroms.

16. (Original) The structure of claim 11 wherein said implanted region is a source/drain extension.

17. (Original) The structure of claim 16 wherein said implanted region is a strained source/drain junction.

18. (Original) The structure of claim 11 including a polysilicon gate.

19. (Original) The structure of claim 18 including a polysilicon gate with side wall spacers.

20. (Original) An integrated circuit comprising:
a semiconductor structure;
a gate formed on said semiconductor structure; and
a source and a drain region, said source and drain region including both germanium and a P-type impurity, said source and drain region being strained.
21. (Original) The circuit of claim 20 wherein the ratio of germanium to P-type impurities is greater than one to one.
22. (Original) The circuit of claim 20 wherein the ratio of germanium to P-type impurities is approximately four to one.
23. (Original) The circuit of claim 20 wherein said P-type impurities are boron impurities.
24. (Original) The circuit of claim 20 wherein said source/drain region that includes both boron and germanium is a source/drain extension.